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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000l-fg144

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 1 – FPGA Array Architecture in Low Power Flash Devices

# **Device Architecture**

#### **Advanced Flash Switch**

Unlike SRAM FPGAs, the low power flash devices use a live-at-power-up ISP flash switch as their programming element. Flash cells are distributed throughout the device to provide nonvolatile, reconfigurable programming to connect signal lines to the appropriate VersaTile inputs and outputs. In the flash switch, two transistors share the floating gate, which stores the programming information (Figure 1-1). One is the sensing transistor, which is only used for writing and verification of the floating gate voltage. The other is the switching transistor. The latter is used to connect or separate routing nets, or to configure VersaTile logic. It is also used to erase the floating gate. Dedicated high-performance lines are connected as required using the flash switch for fast, low-skew, global signal distribution throughout the device core. Maximum core utilization is possible for virtually any design. The use of the flash switch technology also removes the possibility of firm errors, which are increasingly common in SRAM-based FPGAs.



Figure 1-1 • Flash-Based Switch

Flash\*Freeze Technology and Low Power Modes

# Flash\*Freeze Type 2: Control by Dedicated Flash\*Freeze Pin and Internal Logic

The device can be made to enter Flash\*Freeze mode by activating the FF pin together with Microsemi's Flash\*Freeze management IP core (refer to the "Flash\*Freeze Management IP" section on page 36 for more information) or user-defined control logic (Figure 2-3 on page 27) within the FPGA core. This method enables the design to perform important activities before allowing the device to enter Flash\*Freeze mode, such as transitioning into a safe state, completing the processing of a critical event. Designers are encouraged to take advantage of Microsemi's Flash\*Freeze Management IP to handle clean entry and exit of Flash\*Freeze mode (described later in this document). The device will only enter Flash\*Freeze mode when the Flash\*Freeze pin is asserted (active Low) and the User Low Static I<sub>CC</sub> (ULSICC) macro input signal, called the LSICC signal, is asserted (High). One condition is not sufficient to enter Flash\*Freeze mode type 2; both the FF pin and LSICC signal must be asserted.

When Flash\*Freeze type 2 is implemented in the design, the ULSICC macro needs to be instantiated by the user. There are no functional differences in the device whether the ULSICC macro is instantiated or not, and whether the LSICC signal is asserted or deasserted. The LSICC signal is used only to control entering Flash\*Freeze mode. Figure 2-4 on page 27 shows the timing diagram for entering and exiting Flash\*Freeze mode type 2.

After exiting Flash\*Freeze mode type 2 by deasserting the Flash\*Freeze pin, the LSICC signal must be deasserted by the user design. This will prevent entering Flash\*Freeze mode by asserting the Flash\*Freeze pin only.

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Refer to Table 2-3 for Flash\*Freeze (FF) pin and LSICC signal assertion and deassertion values.

Table 2-3 •	Flash*Freeze Mode	Type 1 and 1	ype 2 – Signal As	ssertion and Deassertion v	alues

Signal	Assertion Value	Deassertion Value
Flash*Freeze (FF) pin	Low	High
LSICC signal	High	Low

Notes:

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1. The Flash\*Freeze (FF) pin is an active-Low signal, and LSICC is an active-High signal.

2. The LSICC signal is used only in Flash\*Freeze mode type 2.

Flash\*Freeze Technology and Low Power Modes

power supply and board-level configurations, the user can easily calculate how long it will take for the core to become inactive or active. For more information, refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373.



Figure 2-8 • Entering and Exiting Sleep Mode, Typical Timing Diagram

#### **Context Save and Restore in Sleep or Shutdown Mode**

In Sleep mode or Shutdown mode, the contents of the SRAM, state of the I/Os, and state of the registers are lost when the device is powered off, if no other measure is taken. A low-cost external serial EEPROM can be used to save and restore the contents of the device when entering and exiting Sleep mode or Shutdown mode. In the *Embedded SRAM Initialization Using External Serial EEPROM* application note, detailed information and a reference design are provided for initializing the embedded SRAM using an external serial EEPROM. The user can easily customize the reference design to save and restore the FPGA state when entering and exiting Sleep mode or Shutdown mode. The microcontroller will need to manage this activity; hence, before powering down  $V_{CC}$ , the data will be read from the FPGA and stored externally. In a similar way, after the FPGA is powered up, the microcontroller will allow the FPGA to load the data from external memory and restore its original state.

# Flash\*Freeze Design Guide

This section describes how designers can create reliable designs that use ultra-low power Flash\*Freeze modes optimally. The section below provides guidance on how to select the best Flash\*Freeze mode for any application. The "Design Solutions" section on page 35 gives specific recommendations on how to design and configure clocks, set/reset signals, and I/Os. This section also gives an overview of the design flow and provides details concerning Microsemi's Flash\*Freeze Management IP, which enables clean clock gating and housekeeping. The "Additional Power Conservation Techniques" section on page 41 describes board-level considerations for entering and exiting Flash\*Freeze mode.

#### Selecting the Right Flash\*Freeze Mode

Both Flash\*Freeze modes will bring an FPGA into an ultra-low power static mode that retains register and SRAM content and sets I/Os to a predetermined configuration. There are two primary differences that distinguish type 2 mode from type 1, and they must be considered when creating a design using Flash\*Freeze technology.

First, with type 2 mode, the device has an opportunity to wait for a second signal to enable activation of Flash\*Freeze mode. This allows processes to complete prior to deactivating the device, and can be useful to control task completion, data preservation, accidental Flash\*Freeze activation, system shutdown, or any other housekeeping function. The second signal may be derived from an external or into-out internal source. The second difference between type 1 and type 2 modes is that a design for type 2 mode has an opportunity to cleanly manage clocks and data activity before entering and exiting Flash\*Freeze mode. This is particularly important when data preservation is needed, as it ensures valid data is stored prior to entering, and upon exiting, Flash\*Freeze mode.

Type 1 Flash\*Freeze mode is ideally suited for applications with the following design criteria:

- Entering Flash\*Freeze mode is not dependent on any signal other than the external FF pin.
- Internal housekeeping is not required prior to entering Flash\*Freeze.

#### **Clock Aggregation Architecture**

This clock aggregation feature allows a balanced clock tree, which improves clock skew. The physical regions for clock aggregation are defined from left to right and shift by one spine. For chip global networks, there are three types of clock aggregation available, as shown in Figure 3-10:

- Long lines that can drive up to four adjacent spines (A)
- Long lines that can drive up to two adjacent spines (B)
- Long lines that can drive one spine (C)

There are three types of clock aggregation available for the quadrant spines, as shown in Figure 3-10:

- I/Os or local resources that can drive up to four adjacent spines
- I/Os or local resources that can drive up to two adjacent spines
- I/Os or local resources that can drive one spine

As an example, A3PE600 and AFS600 devices have twelve spine locations: T1, T2, T3, T4, T5, T6, B1, B2, B3, B4, B5, and B6. Table 3-7 shows the clock aggregation you can have in A3PE600 and AFS600.



Figure 3-10 • Four Spines Aggregation

Table 3-7 • Spine Aggregation	in A3PE600 or AFS600
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Clock Aggregation	Spine
1 spine	T1, T2, T3, T4, T5, T6, B1, B2, B3, B4, B5, B6
2 spines	T1:T2, T2:T3, T3:T4, T4:T5, T5:T6, B1:B2, B2:B3, B3:B4, B4:B5, B5:B6
4 spines	B1:B4, B2:B5, B3:B6, T1:T4, T2:T5, T3:T6

The clock aggregation for the quadrant spines can cross over from the left to right quadrant, but not from top to bottom. The quadrant spine assignment T1:T4 is legal, but the quadrant spine assignment T1:B1 is not legal. Note that this clock aggregation is hardwired. You can always assign signals to spine T1 and B2 by instantiating a buffer, but this may add skew in the signal.

Global Resources in Low Power Flash Devices

# **Design Recommendations**

The following sections provide design flow recommendations for using a global network in a design.

- "Global Macros and I/O Standards"
- "Global Macro and Placement Selections" on page 64
- "Using Global Macros in Synplicity" on page 66
- "Global Promotion and Demotion Using PDC" on page 67
- "Spine Assignment" on page 68
- "Designer Flow for Global Assignment" on page 69
- "Simple Design Example" on page 71
- "Global Management in PLL Design" on page 73
- "Using Spines of Occupied Global Networks" on page 74

#### **Global Macros and I/O Standards**

The larger low power flash devices have six chip global networks and four quadrant global networks. However, the same clock macros are used for assigning signals to chip globals and quadrant globals. Depending on the clock macro placement or assignment in the Physical Design Constraint (PDC) file or MultiView Navigator (MVN), the signal will use the chip global network or quadrant network. Table 3-8 lists the clock macros available for low power flash devices. Refer to the *IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide* for details.

I ADIE 3-8 • CIOCK MACTO	Table	3-8	Clock	Macros
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Macro Name	Description	Symbol
CLKBUF	Input macro for Clock Network	
CLKBUF_x	Input macro for Clock Network with specific I/O standard	
CLKBUF_LVDS/LVPECL	LVDS or LVPECL input macro for Clock Network (not supported for IGLOO nano or ProASIC3 nano devices)	PADP CLKBUF
CLKINT	Macro for internal clock interface	
CLKBIBUF	Bidirectional macro with input dedicated to routed Clock Network	

Use these available macros to assign a signal to the global network. In addition to these global macros, PLL and CLKDLY macros can also drive the global networks. Use I/O–standard–specific clock macros (CLKBUF\_x) to instantiate a specific I/O standard for the global signals. Table 3-9 on page 63 shows the list of these I/O–standard–specific macros. Note that if you use these I/O–standard–specific clock macros, you cannot change the I/O standard later in the design stage. If you use the regular CLKBUF macro, you can use MVN or the PDC file in Designer to change the I/O standard. The default I/O

ProASIC3L FPGA Fabric User's Guide



Figure 3-12 • Chip Global Region



Figure 3-13 • Quadrant Global Region

#### Simple Design Example

Consider a design consisting of six building blocks (shift registers) and targeted for an A3PE600-PQ208 (Figure 3-16 on page 68). The example design consists of two PLLs (PLL1 has GLA only; PLL2 has both GLA and GLB), a global reset (ACLR), an enable (EN\_ALL), and three external clock domains (QCLK1, QCLK2, and QCLK3) driving the different blocks of the design. Note that the PQ208 package only has two PLLs (which access the chip global network). Because of fanout, the global reset and enable signals need to be assigned to the chip global resources. There is only one free chip global for the remaining global (QCLK1, QCLK2, QCLK3). Place two of these signals on the quadrant global resource. The design example demonstrates manually assignment of QCLK1 and QCLK2 to the quadrant global using the PDC command.



Figure 3-19 • Block Diagram of the Global Management Example Design

### **Fusion CCC Locations**

Fusion devices have six CCCs: one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-17 and Figure 4-18). The device can have one integrated PLL in the middle of the west side of the device or two integrated PLLs in the middle of the east and west sides of the device (middle right and middle left).



*Figure 4-17* • CCC Locations in Fusion Family Devices (AFS090, AFS250, M1AFS250)



Figure 4-18 • CCC Locations in Fusion Family Devices (except AFS090, AFS250, M1AFS250)

# 5 – FlashROM in Microsemi's Low Power Flash Devices

### Introduction

The Fusion, IGLOO, and ProASIC3 families of low power flash-based devices have a dedicated nonvolatile FlashROM memory of 1,024 bits, which provides a unique feature in the FPGA market. The FlashROM can be read, modified, and written using the JTAG (or UJTAG) interface. It can be read but not modified from the FPGA core. Only low power flash devices contain on-chip user nonvolatile memory (NVM).

# Architecture of User Nonvolatile FlashROM

Low power flash devices have 1 kbit of user-accessible nonvolatile flash memory on-chip that can be read from the FPGA core fabric. The FlashROM is arranged in eight banks of 128 bits (16 bytes) during programming. The 128 bits in each bank are addressable as 16 bytes during the read-back of the FlashROM from the FPGA core. Figure 5-1 shows the FlashROM logical structure.

The FlashROM can only be programmed via the IEEE 1532 JTAG port. It cannot be programmed directly from the FPGA core. When programming, each of the eight 128-bit banks can be selectively reprogrammed. The FlashROM can only be reprogrammed on a bank boundary. Programming involves an automatic, on-chip bank erase prior to reprogramming the bank. The FlashROM supports synchronous read. The address is latched on the rising edge of the clock, and the new output data is stable after the falling edge of the same clock cycle. For more information, refer to the timing diagrams in the DC and Switching Characteristics chapter of the appropriate datasheet. The FlashROM can be read on byte boundaries. The upper three bits of the FlashROM address from the FPGA core define the bank being accessed. The lower four bits of the FlashROM address from the FPGA core define which of the 16 bytes in the bank is being accessed.

		Byte	Byte Number in Bank						4 LSB of ADDR (READ)								
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
of	7																
SB	6																
AD M	5																
(RE	4																
dm SR (	3																
ADI	2																
ank	1																
ä	0																

Figure 5-1 • FlashROM Architecture

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices



Notes:

- Automotive ProASIC3 devices restrict RAM4K9 to a single port or to dual ports with the same clock 180° out of phase (inverted) between clock pins. In single-port mode, inputs to port B should be tied to ground to prevent errors during compile. This warning applies only to automotive ProASIC3 parts of certain revisions and earlier. Contact Technical Support at soc\_tech@microsemi.com for information on the revision number for a particular lot and date code.
- 2. For FIFO4K18, the same clock 180° out of phase (inverted) between clock pins should be used.

Figure 6-3 • Supported Basic RAM Macros

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

# Software Support

The SmartGen core generator is the easiest way to select and configure the memory blocks (Figure 6-12). SmartGen automatically selects the proper memory block type and aspect ratio, and cascades the memory blocks based on the user's selection. SmartGen also configures any additional signals that may require tie-off.

SmartGen will attempt to use the minimum number of blocks required to implement the desired memory. When cascading, SmartGen will configure the memory for width before configuring for depth. For example, if the user requests a 256×8 FIFO, SmartGen will use a 512×9 FIFO configuration, not 256×18.

Figure 6-12 • SmartGen Core Generator Interface

SmartGen enables the user to configure the desired RAM element to use either a single clock for read and write, or two independent clocks for read and write. The user can select the type of RAM as well as the width/depth and several other parameters (Figure 6-13).

#### Figure 6-13 • SmartGen Memory Configuration Interface

SmartGen also has a Port Mapping option that allows the user to specify the names of the ports generated in the memory block (Figure 6-14).

#### *Figure 6-14* • Port Mapping Interface for SmartGen-Generated Memory

SmartGen also configures the FIFO according to user specifications. Users can select no flags, static flags, or dynamic flags. Static flag settings are configured using configuration flash and cannot be altered

# I/O Architecture

#### I/O Tile

The I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired (Figure 7-2). The registers can also be used to support the JESD-79C Double Data Rate (DDR) standard within the I/O structure (see the "DDR for Microsemi's Low Power Flash Devices" section on page 271 for more information). In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired (Figure 7-2).

As depicted in Figure 7-2, all I/O registers share one CLR port. The output register and output enable register share one CLK port.



Figure 7-2 • DDR Configured I/O Block Logical Representation

I/O Software Control in Low Power Flash Devices

#### Instantiating in HDL code

All the supported I/O macros can be instantiated in the top-level HDL code (refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, *and Fusion Macro Library Guide* for a detailed list of all I/O macros). The following is an example:

```
library ieee;
use ieee.std_logic_1164.all;
library proasic3e;
entity TOP is
 port(IN2, IN1 : in std_logic; OUT1 : out std_logic);
end TOP;
architecture DEF_ARCH of TOP is
  component INBUF_LVCMOS5U
    port(PAD : in std_logic := 'U'; Y : out std_logic);
  end component;
  component INBUF_LVCMOS5
   port(PAD : in std_logic := 'U'; Y : out std_logic);
  end component;
  component OUTBUF_SSTL3_II
    port(D : in std_logic := 'U'; PAD : out std_logic);
  end component;
  Other component ....
signal x, y, z.....other signals : std_logic;
begin
  I1 : INBUF_LVCMOS5U
   port map(PAD => IN1, Y =>x);
  12 : INBUF LVCMOS5
   port map(PAD => IN2, Y => y);
  I3 : OUTBUF_SSTL3_II
    port map(D => z, PAD => OUT1);
```

other port mapping ...

end DEF\_ARCH;

#### Synthesizing the Design

Libero SoC integrates with the Synplify<sup>®</sup> synthesis tool. Other synthesis tools can also be used with Libero SoC. Refer to the *Libero SoC User's Guide* or Libero online help for details on how to set up the Libero tool profile with synthesis tools from other vendors.

During synthesis, the following rules apply:

- Generic macros:
  - Users can instantiate generic INBUF, OUTBUF, TRIBUF, and BIBUF macros.
  - Synthesis will automatically infer generic I/O macros.
  - The default I/O technology for these macros is LVTTL.
  - Users will need to use the I/O Attribute Editor in Designer to change the default I/O standard if needed (see Figure 9-6 on page 259).
- Technology-specific I/O macros:
  - Technology-specific I/O macros, such as INBUF\_LVCMO25 and OUTBUF\_GTL25, can be instantiated in the design. Synthesis will infer these I/O macros in the netlist.

### **Compiling the Design**

During Compile, a PDC I/O constraint file can be imported along with the netlist file. If only the netlist file is compiled, certain I/O assignments need to be completed before proceeding to Layout. All constraints that can be entered in PDC can also be entered using ChipPlanner, I/O Attribute Editor, and PinEditor.

There are certain rules that must be followed in implementing I/O register combining and the I/O DDR macro (refer to the I/O Registers section of the handbook for the device that you are using and the "DDR" section on page 256 for details). Provided these rules are met, the user can enable or disable I/O register combining by using the PDC command set\_io portname -register yes |no in the I/O Attribute Editor or selecting a check box in the Compile Options dialog box (see Figure 9-7). The Compile Options dialog box appears when the design is compiled for the first time. It can also be accessed by choosing **Options** > **Compile** during successive runs. I/O register combining is off by default. The PDC command overrides the setting in the Compile Options dialog box.

Figure 9-7 • Setting Register Combining During Compile

#### Understanding the Compile Report

The I/O bank report is generated during Compile and displayed in the log window. This report lists the I/O assignments necessary before Layout can proceed.

When Designer is started, the I/O Bank Assigner tool is run automatically if the Layout command is executed. The I/O Bank Assigner takes care of the necessary I/O assignments. However, these assignments can also be made manually with MVN or by importing the PDC file. Refer to the "Assigning Technologies and VREF to I/O Banks" section on page 264 for further description.

The I/O bank report can also be extracted from Designer by choosing **Tools** > **Report** and setting the Report Type to **IOBank**.

This report has the following tables: I/O Function, I/O Technology, I/O Bank Resource Usage, and I/O Voltage Usage. This report is useful if the user wants to do I/O assignments manually.

I/O Software Control in Low Power Flash Devices

# List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page				
August 2012	The notes in Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to clarify which device families support programmable input delay (SAR 39666).	253				
June 2011	Figure 9-2 • SmartGen Catalog was updated (SAR 24310). Figure 8-3 • Expanded I/O Section and the step associated with it were deleted to reflect changes in the software.					
	The following rule was added to the "VREF Rules for the Implementation of Voltage-Referenced I/O Standards" section:	265				
	Only minibanks that contain input or bidirectional I/Os require a VREF. A VREF is not needed for minibanks composed of output or tristated I/Os (SAR 24310).	I				
July 2010	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A				
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	252				
	The notes for Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to indicate that skew control and input delay do not apply to nano devices.	253				
v1.3 (October 2008)	The "Flash FPGAs I/O Support" section was revised to include new families and make the information more concise.	252				
v1.2 (June 2008)	<ul> <li>The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs:</li> <li>ProASIC3L was updated to include 1.5 V.</li> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	252				
v1.1 (March 2008)	This document was previously part of the <i>I/O Structures in IGLOO and ProASIC3 Devices</i> document. The content was separated and made into a new document.	N/A				
	Table 9-2 • Designer State (resulting from I/O attribute modification) was updated to include note 2 for IGLOO PLUS.	253				

DDR for Microsemi's Low Power Flash Devices

# **DDR Support in Flash-Based Devices**

The flash FPGAs listed in Table 10-1 support the DDR feature and the functions described in this document.

#### Table 10-1 • Flash-Based FPGAs

Series	Family <sup>*</sup>	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex <sup>™</sup> -M1 soft processors, and flash memory into a monolithic device

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

#### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 10-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

#### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 10-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

# 12 – Security in Low Power Flash Devices

# Security in Programmable Logic

The need for security on FPGA programmable logic devices (PLDs) has never been greater than today. If the contents of the FPGA can be read by an external source, the intellectual property (IP) of the system is vulnerable to unauthorized copying. Fusion, IGLOO, and ProASIC3 devices contain state-of-the-art circuitry to make the flash-based devices secure during and after programming. Low power flash devices have a built-in 128-bit Advanced Encryption Standard (AES) decryption core (except for 30 k gate devices and smaller). The decryption core facilitates secure in-system programming (ISP) of the FPGA core array fabric, the FlashROM, and the Flash Memory Blocks (FBs) in Fusion devices. The FlashROM, Flash Blocks, and FPGA core fabric can be programmed independently of each other, allowing the FlashROM or Flash Blocks to be updated without the need for change to the FPGA core fabric.

Microsemi has incorporated the AES decryption core into the low power flash devices and has also included the Microsemi flash-based lock technology, FlashLock.<sup>®</sup> Together, they provide leading-edge security in a programmable logic device. Configuration data loaded into a device can be decrypted prior to being written to the FPGA core using the AES 128-bit block cipher standard. The AES encryption key is stored in on-chip, nonvolatile flash memory.

This document outlines the security features offered in low power flash devices, some applications and uses, as well as the different software settings for each application.

Figure 12-1 • Overview on Security

Security in Low Power Flash Devices



Note: If programming the Security Header only, just perform sub-flow 1. If programming design content only, just perform sub-flow 2.

Figure 12-9 • Security Programming Flows



Security in Low Power Flash Devices

#### **STAPL File with AES Encryption**

- Does not contain AES key / FlashLock Key information
- · Intended for transmission through web or service to unsecured locations for programming

```
NOTE "CREATOR" "Designer Version: 6.1.1.108";
NOTE "DEVICE" "A3PE600";
NOTE "DACKAGE" "208 PQFP";
NOTE "DATE" "2005/04/08";
NOTE "DATE" "2005/04/08";
NOTE "STAPL_VERSION" "JESD71";
NOTE "IDCODE" "$123261CF";
NOTE "DESIGN" "counter32";
NOTE "DESIGN" "counter32";
NOTE "CHECKSUM" "$EF57";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SECURITY" "ENCRYPT FROM CORE ";
NOTE "ALG_VERSION" "1";
NOTE "MAX_FREQ" "20000000";
NOTE "SILSIG" "$00000000";
```

### Conclusion

The new and enhanced security features offered in Fusion, IGLOO, and ProASIC3 devices provide stateof-the-art security to designs programmed into these flash-based devices. Microsemi low power flash devices employ the encryption standard used by NIST and the U.S. government—AES using the 128-bit Rijndael algorithm.

The combination of an on-chip AES decryption engine and FlashLock technology provides the highest level of security against invasive attacks and design theft, implementing the most robust and secure ISP solution. These security features protect IP within the FPGA and protect the system from cloning, wholesale "black box" copying of a design, invasive attacks, and explicit IP or data theft.

Term	Explanation
Security Header programming file	Programming file used to program the FlashLock Pass Key and/or AES key into the device to secure the FPGA, FlashROM, and/or FBs.
AES (encryption) key	128-bit key defined by the user when the AES encryption option is set in the Microsemi Designer software when generating the programming file.
FlashLock Pass Key	128-bit key defined by the user when the FlashLock option is set in the Microsemi Designer software when generating the programming file.
	The FlashLock Key protects the security settings programmed to the device. Once a device is programmed with FlashLock, whatever settings were chosen at that time are secure.
FlashLock	The combined security features that protect the device content from attacks. These features are the following:
	Flash technology that does not require an external bitstream to program the device
	<ul> <li>FlashLock Pass Key that secures device content by locking the security settings and preventing access to the device as defined by the user</li> </ul>
	<ul> <li>AES key that allows secure, encrypted device reprogrammability</li> </ul>

# Glossary

# References

National Institute of Standards and Technology. "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers." 28 January 2002 (10 January 2005).

See http://csrc.nist.gov/archive/aes/index1.html for more information.